

一、 描述 / Descriptions

VRW056 硅 NPN 三极管 SOT-23 封装 Silicon NPN transistor in a SOT-23 Plastic Package.

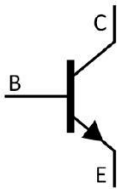
二、 特性 / Features

高电压，高电流，高 h_{FE} ，低噪声，优异的 h_{FE} 线性度，符合 AEC-Q101 标准，高可靠性，HF 产品。

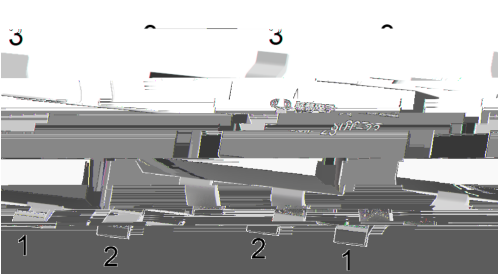
三、 应用 / Applications

音频频率通用放大器应用，满足汽车应用的要求。

四、 等效电路 / Equivalent Circuit



五、 引脚 / Pinning



PIN1 基极 Base PIN 2 发射极 Emitter PIN 3 集电极 Collector

六、 h_{FE} 分类及标识 / h_{FE} Classifications & Marking

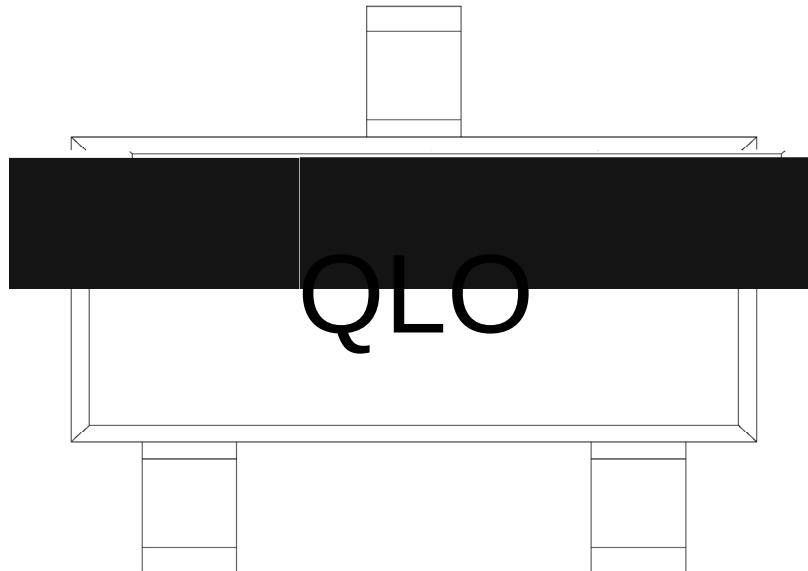
h_{FE} Classifications Symbol	O	Y	GR	BL
h_{FE} Range	70 140	120 240	200 400	350 700
Marking	QLO	QLY	QLG	QLL



Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	60	V
Collector to Emitter Voltage	V_{CEO}	50	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current	I_C	150	mA
Base Current	I_B	30	mA
Collector Power Dissipation	P_C	150	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-Off Current	I_{CBO}	$V_{CB}=60V$ $I_E=0$			0.1	μA
Emitter Base Cut-Off Current	I_{EBO}	$V_{EB}=5.0V$ $I_C=0$			0.1	μA
DC Current Gain	h_{FE}	$V_{CE}=6.0V$ $I_C=2.0mA$	70		700	
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=100mA$ $I_B=10mA$		0.1	0.25	V

1. 1.1 / Marking Instructions



1.1.1

T: 额定功率 P_{DM} (%)

0: 额定功率 P_{DM}

R: h_{FE} 等级

Note:

T: 额定功率 P_{DM} (%)

0: Product Type Code

R: h_{FE} Classifications Symbol



Whp shudwxuh Suriloh i ru LU Uhior z Vroghulqj+Se0luhh,

ب " χ

Note:

1 150 K 200 t i`H j 60 K 120sec;

1.Preheating:150~200 t , Time:60~120sec.

2 Š Œ □ ŷ 255 ° 5 t i`H j`Y 1 5 ° 0.5sec;

2.Peak Temp.:255 ° 5 t , Duration:5 ° 0.5sec.

3 i` 2 K 10 t /sec.

3.Cooling Speed: 2~10 t /sec.

Resistance to Soldering Heat Test Conditions

□ ŷ χ 260 ° 5 t

`H j χ 10 ° 1 sec.

Temp.:260±5

Time:10±1 sec

Packaging SPEC.

REEL

Package Type	Units				Dimension	(unit mm ³)
	Units/Reel	Reels/Inner Box	Units/Inner Box	Inner Boxes/Outer Box		